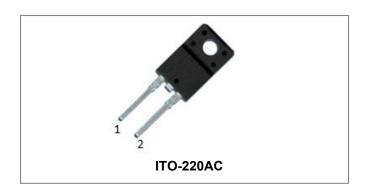






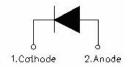
MURF1060 ULTRAFAST RECTIFIER



Features

- Ultra-Fast Switching
- High Current Capability
- Low Reverse Leakage Current
- High Surge Current Capability
- Plastic Material has UL Flammability Classification 94V-O
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching Power Supply
- Power Switching Circuits
- General Purpose

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ \end{array}$	-	600	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=100°C, rectangular wave form	10	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse	125	А

Electrical Characteristics:

Characteristics	Symbol Condition		Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@10A, Pulse, T _J = 25°C	1.25	2.2	V
	V _{F2}	@10A, Pulse, T _J = 100°C	-	2.0	V
Reverse Current*	I _{R1}	$@V_R = \text{rated } V_R$ $T_J = 25^{\circ}C$	0.03	5	μА
	I _{R2}	$@V_R = \text{rated } V_R$ $T_J = 100^{\circ}\text{C}$	-	50	μА
Reverse Recovery Time	t_{rr} I_F =500mA, I_R =1A,and I_m =250mA		43	50	ns
RSM Isolation Voltage (t=1.0 second,R.H.< =30%,		Clip mouting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	-	4500	
T _A =25°C)	V _{1so}	Clip mouting, the epoxy body is inside the heatsink	-	3500	V
		Screw mounting, the epoxy body is inside the heatsink	-	1500	

^{*} Pulse width < 300 µs, duty cycle < 2%

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Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R _θ Jc	DC operation	4	°C/W
Approximate Weight	wt	-	1.6	g
Case Style	ITO-220AC			

Ratings and Characteristics Curves

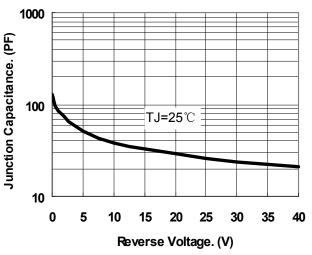


Fig.1-Typical Junction Capacitance

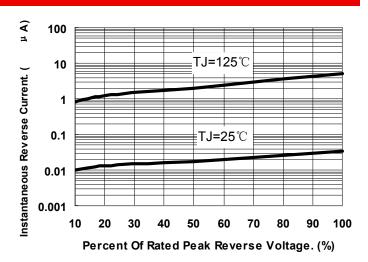


Fig.2-Typical Reverse Characteristics

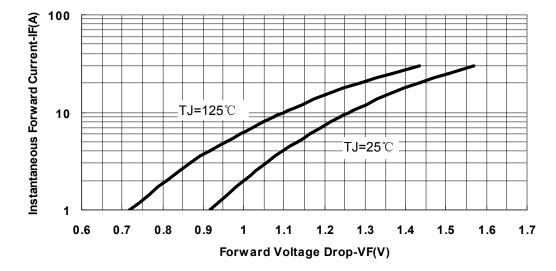


Fig.3-Typical Forward Voltage Drop Characteristics

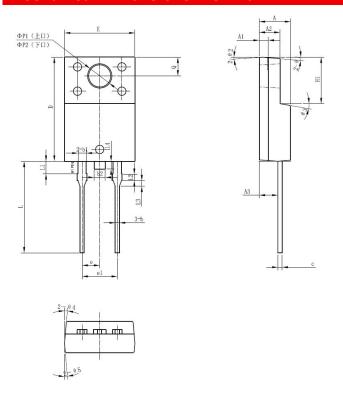
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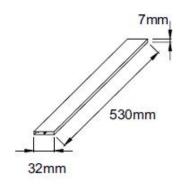


Mechanical Dimensions ITO-220AC



CVMDOL	Millimeters				
SYMBOL	MIN.	TYP.	MAX.		
Α	4.30	4.50	4.70		
A1	1.10	1.30	1.50		
A2	2.80	3.00	3.20		
A3	2.50	2.70	2.90		
b	0.50	0.60	0.75		
b1	1.10	1.20	1.35		
b2	1.50	1.60	1.75		
С	0.50	0.60	0.75		
D	14.80	15.00	15.20		
E	9.96	10.16	10.36		
е	ı	2.55	-		
e1	5.00	5.10	5.16		
H1	6.50	6.70	6.90		
L	12.70	13.20	13.70		
L1	1.60	1.80	2.00		
L2	0.80	1.00	1.20		
L3	0.60	0.80	1.00		
L4	-	1.10	1.50		
ΦP1 (上口)	3.30	3.50	3.70		
ΦP2 (下口)	2.99	3.19	3.39		
Q	2.50	2.70	2.90		
Θ1		5°			
Θ2		4°			
Θ3		10°			
Θ4		5°			
Θ5		5°			

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

MUR = Device Type
F = Package type
10 = Forward Current (10A)
60 = Reverse Voltage (600V)
SSG = SSG

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping	
MURF1060	ITO-220AC (Pb-Free)	50 pcs/ tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification

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